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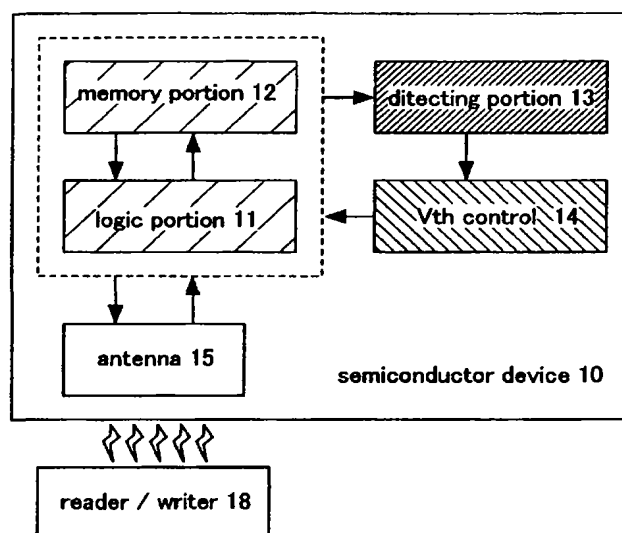
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(54) Title: SEMICONDUCTOR DEVICE



(57) Abstract: The invention provides a semiconductor device that power is stabilized by suppressing power consumption as much as possible. The semiconductor device of the invention includes a logic portion and a memory portion each including a plurality of transistors, a detecting portion for detecting one or both of operation frequencies of the logic portion and the memory portion, a Vth control for supplying a Vth control signal to one or both of the logic portion and the memory portion, and an antenna. Each of the plurality of transistors has a first gate electrode which is input with a logic signal, a second gate electrode which is input with the Vth control signal, and a semiconductor film such that the second gate electrode, the semiconductor film, and the first gate electrode are provided in this order from the bottom.